

Inotera announces the successful pilot run of its 300 mm production facility

June 30 2004

Inotera Memories, Inc., a joint venture by Infineon Technologies AG and Nanya Technology Corporation, announced the successful completion of its first pilot lot of 300mm (12-inch) wafers based on 110nm DRAM trench technology. The first product manufactured at Inotera's fab is an Infineon-designed 256Mbit DDR SDRAM. Additional DRAM products are planned to follow later this year.

Inotera has executed the construction and ramp up according to schedule in a very short time frame. After the completion of the clean room in 2003, equipment move-in starting in December, 2003, followed by the first pilot lot out in April, 2004.

The initial testing results confirmed the processing as well as the equipment capabilities and performance. Inotera is now ready to move into the next stage of volume ramp up to monthly wafer starts of around 24,000 by the end of 2004. In the second stage –expected to be completed by the end of 2005, a total capacity of around 54,000 wafer starts per month is expected to be reached, making Inotera one of the world's largest 300mm semiconductor facilities.

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